Silicon NPN Power Transistors 2SD1294

DESCRIPTION

- With TO-3P(I) package
- Wide area of safe operation
- High DC current gain
- Darlington

APPLICATIONS

- Power regulator for line operated TV

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

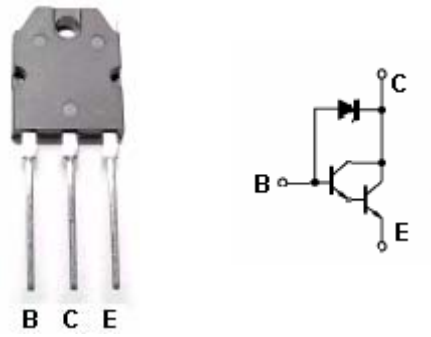

Fig.1 simplified outline (TO-3P(I)) and symbol

Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	60±15	V
V_{CEO}	Collector-emitter voltage	Open base	60±15	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current (DC)		5	A
I_{CP}	Collector current (Pulse)		20	A
P_C	Collector power dissipation	T_C=25℃	80	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEO}	Collector-emitter breakdown voltage	I_C=100mA ;I_B=0	45		75	V
V_{CBO}	Collector-base breakdown voltage	I_C=100mA ;I_E=0	45		75	V
$V_{CEsat-1}$	Collector-emitter saturation voltage	I_C=0.5A ;I_B=1mA			1.5	V
$V_{CEsat-2}$	Collector-emitter saturation voltage	I_C=1A; I_B=1mA			2.5	V
V_{BE}	Base-emitter on voltage	I_C=0.5A;V_{CE}=5V			1.8	V
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=0.5A ; V_{CE}=5V	2000		20000	

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PACKAGE OUTLINE

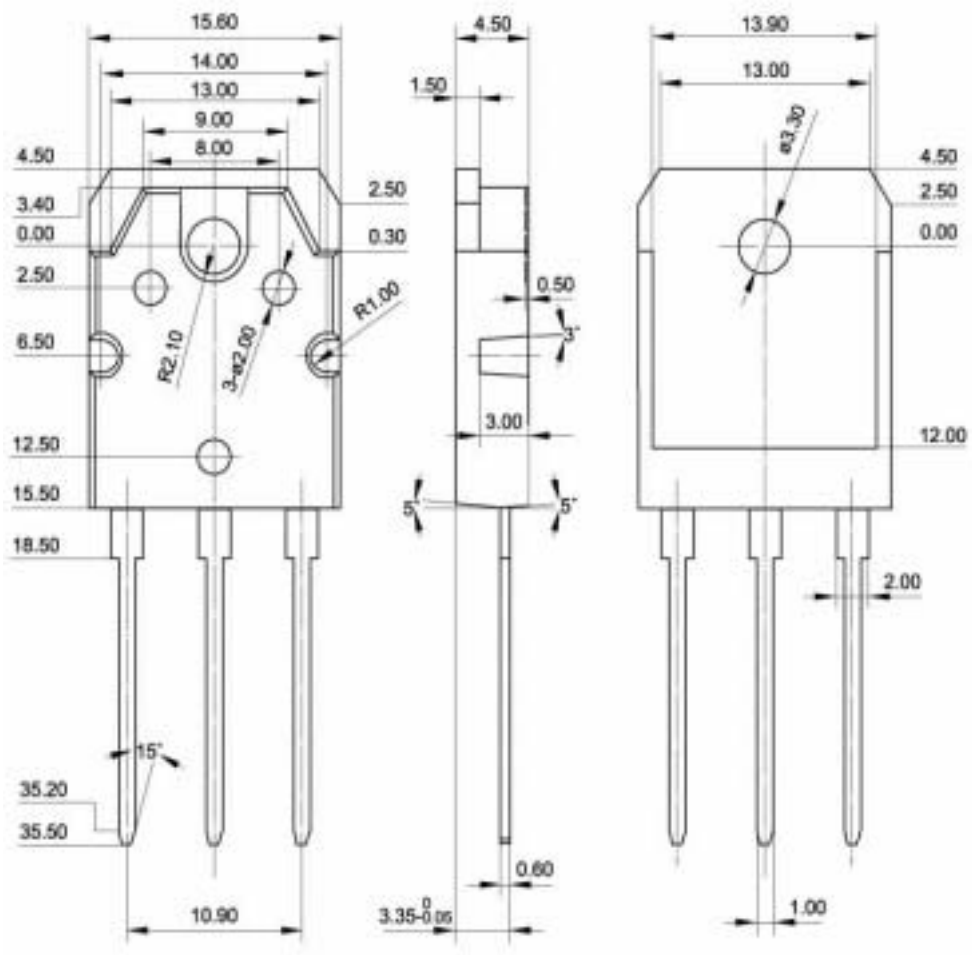

Fig.2 outline dimentions